

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE ( $\pi$ -MOSII)

# 2SK1642

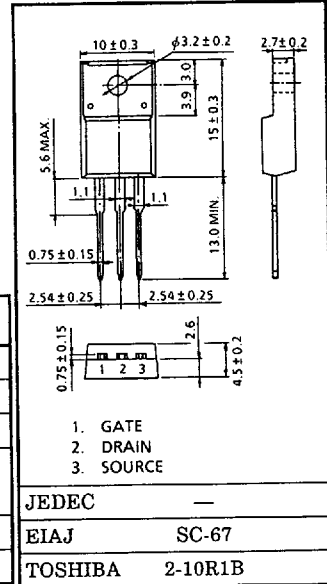
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS.  
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS.

INDUSTRIAL APPLICATIONS  
Unit in mm

- Low Drain-Source ON Resistance :  $R_{DS(ON)} = 0.35\Omega$  (Typ.)
- High Forward Transfer Admittance :  $|Y_{fs}| = 5.0S$  (Typ.)
- Low Leakage Current :  $I_{DSS} = 300\mu A$  (Max.) @  $V_{DS} = 400V$
- Enhancement-Mode :  $V_{th} = 2.0 \sim 4.0V$  @  $V_{DS} = 10V, I_D = 1mA$

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		$V_{DSS}$	400	V
Drain-Gate Voltage ( $R_{GS} = 20k\Omega$ )		$V_{DGR}$	400	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	DC	$I_D$	9	A
	Pulse	$I_{DP}$	36	
Drain Power Dissipation ( $T_c = 25^\circ C$ )		$P_D$	45	W
Channel Temperature		$T_{ch}$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	$-55 \sim 150$	$^\circ C$



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B
Weight : 1.9g	

HERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	2.77	$^\circ C/W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE. PLEASE HANDLE WITH CAUTION.

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current		$I_{GSS}$	$V_{GS} = \pm 25V, V_{DS} = 0V$	—	—	$\pm 100$	nA	
Drain Cut-off Current		$I_{DSS}$	$V_{DS} = 400V, V_{GS} = 0V$	—	—	300	$\mu A$	
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$I_D = 10mA, V_{GS} = 0V$	400	—	—	V	
Gate Threshold Voltage		$V_{th}$	$V_{DS} = 10V, I_D = 1mA$	2.0	—	4.0	V	
Drain-Source ON Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 5A$	—	0.35	0.55	$\Omega$	
Forward Transfer Admittance		$ Y_{fs} $	$V_{DS} = 10V, I_D = 5A$	3.0	5.0	—	S	
Input Capacitance		$C_{iss}$		—	1250	—	pF	
Reverse Transfer Capacitance		$C_{rss}$		$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	—	55		—
Output Capacitance		$C_{oss}$		—	170	—		
Switching Time	Rise Time	$t_r$	$V_{IN} : t_r, t_f < 5ns, V_{DD} = 225V$ Duty $\leq 1\%, t_w = 10\mu s$	—	25	—	ns	
	Turn-on Time	$t_{on}$		—	40	—		
	Fall Time	$t_f$		—	32	—		
	Turn-off Time	$t_{off}$		—	100	—		
Total Gate Charge (Gate-Source Plus Gate-Drain)		$Q_g$	$V_{DD} = 320V, V_{GS} = 10V,$ $I_D = 9A$	—	55	—	nC	
Gate-Source Charge		$Q_{gs}$		—	32	—		
Gate-Drain ("Miller") Charge		$Q_{gd}$		—	23	—		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	$I_{DR}$	—	—	—	9	A
Pulse Drain Reverse Current	$I_{DRP}$	—	—	—	36	A
Diode Forward Voltage	$V_{DSF}$	$I_{DR} = 9A, V_{GS} = 0V$	—	-1.2	-2.0	V

